

# RJF0611JPE

# Silicon N Channel MOS FET Series Power Switching

R07DS0582EJ0200 Rev.2.00 Apr 13, 2012

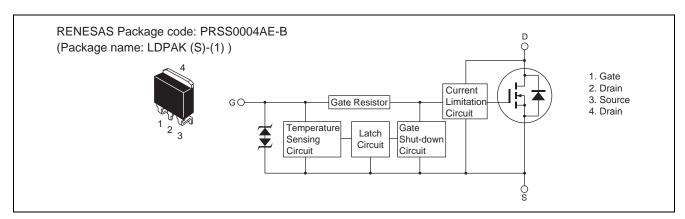
#### **Description**

This FET has the over temperature shut-down capability sensing to the junction temperature. This FET has the built-in over temperature shut-down circuit in the gate area. And this circuit operation to shut-down the gate voltage in case of high junction temperature like applying over power consumption, over current etc..

#### **Features**

- Logic level operation (4 V Gate drive).
- Built-in the over temperature shut-down circuit.
- High endurance capability against to the short circuit.
- Latch type shut down operation (need 0 voltage recovery).
- Built-in the current limitation circuit.
- Power supply voltage applies 12 V and 24 V.
- AEC-Q101 Compliant

#### **Outline**



## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	60	V
Gate to source voltage	$V_{GSS}$	16	V
Gate to source voltage	$V_{GSS}$	-2.5	V
Drain current	I <sub>D</sub> Note3	30	А
Body-drain diode reverse drain current	I <sub>DR</sub>	30	А
Avalanche current	I <sub>AP</sub> Note 2	6.7	А
Avalanche energy	E <sub>AR</sub> Note 2	192	mJ
Channel dissipation	Pch Note 1	50	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. Value at Tc = 25°C

- 2. Tch = 25°C, Rg  $\geq$  50  $\Omega$
- 3. It provides by the current limitation lower bound value.

# **Typical Operation Characteristics**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Input voltage	V <sub>IH</sub>	3.5	_	_	V	
	$V_{IL}$	_	_	1.2	V	
Input current	I <sub>IH1</sub>	1	_	100	μΑ	$Vi = 8 V, V_{DS} = 0$
(Gate non shut down)	I <sub>IH2</sub>	1	_	50	μΑ	$Vi = 3.5 V, V_{DS} = 0$
	I <sub>IL</sub>	1	_	1	μΑ	Vi = 1.2 V, V <sub>DS</sub> = 0
Input current	I <sub>IH(sd)1</sub>	1	0.8	_	mA	$Vi = 8 V, V_{DS} = 0$
(Gate shut down)	I <sub>IH(sd)2</sub>	1	0.35	_	mA	$Vi = 3.5 V, V_{DS} = 0$
Shut down temperature	Tsd	1	175	_	°C	Channel temperature
Gate operation voltage	Vop	3.5	_	12	V	
Drain current	I <sub>D limt</sub>	30	_	_	Α	$V_{GS} = 5 \text{ V}, V_{DS} = 10 \text{ V}^{\text{Note 4}}$
(Current limitation value)						

Note; 4. Pulse test

### **Electrical Characteristics**

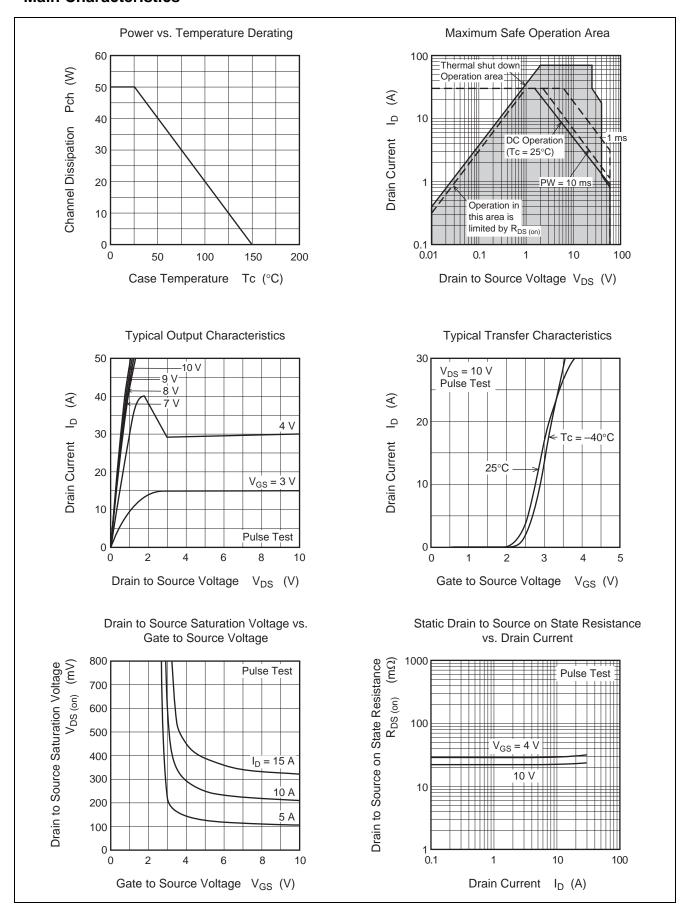
 $(Ta = 25^{\circ}C)$ 

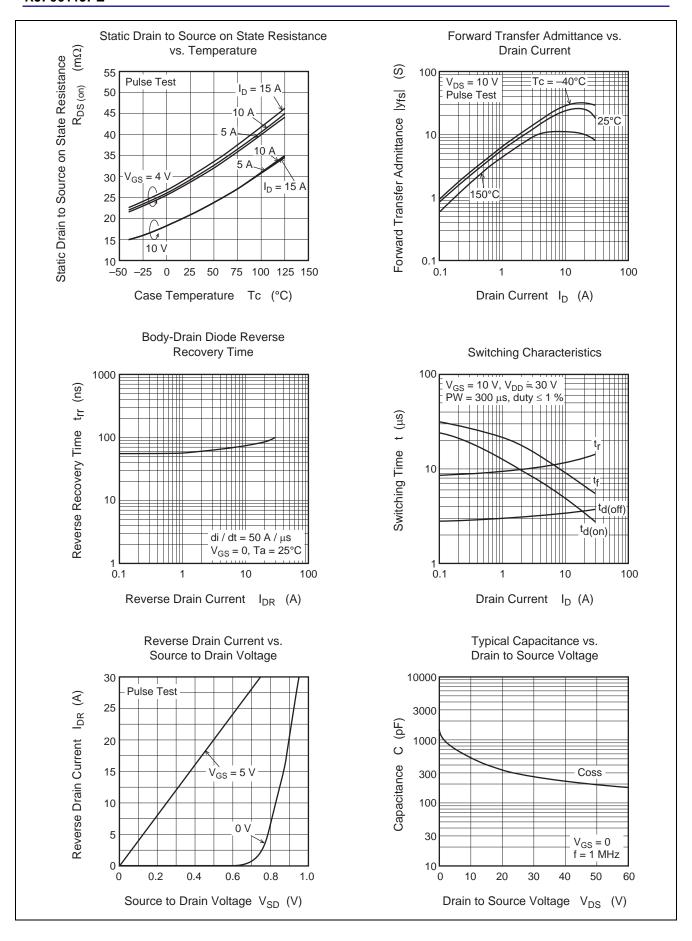
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain current	I <sub>D1</sub>	_	_	45	Α	$V_{GS} = 3.5 \text{ V}, V_{DS} = 10 \text{ V}$
	I <sub>D2</sub>	_	_	10	mA	V <sub>GS</sub> = 1.2 V, V <sub>DS</sub> = 10 V
	I <sub>D3</sub>	30	_	_	Α	$V_{GS} = 5 \text{ V}, V_{DS} = 10 \text{ V}^{\text{Note 5}}$
Drain to source breakdown	$V_{(BR)DSS}$	60	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
voltage						
Gate to source breakdown	$V_{(BR)GSS}$	16	_	_	V	$I_G = 800 \ \mu A, \ V_{DS} = 0$
voltage	$V_{(BR)GSS}$	-2.5	_	_	V	$I_G = -100 \mu A, V_{DS} = 0$
Gate to source leak current	I <sub>GSS1</sub>	_	_	100	μΑ	$V_{GS} = 8 \text{ V}, V_{DS} = 0$
	$I_{GSS2}$	_	_	50	μΑ	$V_{GS} = 3.5 \text{ V}, V_{DS} = 0$
	I <sub>GSS3</sub>	_	_	1	μΑ	$V_{GS} = 1.2 \text{ V}, V_{DS} = 0$
	I <sub>GSS4</sub>	_	_	-100	μΑ	$V_{GS} = -2.4 \text{ V}, V_{DS} = 0$
Input current (shut down)	I <sub>GS(OP)1</sub>	_	0.8	_	mA	$V_{GS} = 8 \text{ V}, V_{DS} = 0$
	I <sub>GS(OP)2</sub>	_	0.35	_	mA	$V_{GS} = 3.5 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	10	μΑ	$V_{DS} = 32 \text{ V}, V_{GS} = 0, Tc = 110^{\circ}\text{C}$
Gate to source cutoff voltage	$V_{GS(off)}$	1.1	_	2.1	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Forward transfer admittance	y <sub>fs</sub>	12	27	_	S	$I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note 5}}$
Static drain to source on state	R <sub>DS(on)</sub>	_	30	40	mΩ	$I_D = 15 \text{ A}, V_{GS} = 4 \text{ V}^{\text{Note 5}}$
resistance	R <sub>DS(on)</sub>	_	21	30	mΩ	$I_D = 15 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note 5}}$
Output capacitance	Coss	_	523	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{MHz}$
Turn-on delay time	t <sub>d(on)</sub>	_	3.8	_	μS	$V_{GS} = 10 \text{ V}, I_{D} = 15 \text{ A}, R_{L} = 2 \Omega$
Rise time	t <sub>r</sub>	_	13.5	_	μS	
Turn-off delay time	t <sub>d(off)</sub>	_	4.1	_	μS	
Fall time	t <sub>f</sub>	_	7.3	_	μS	]
Body-drain diode forward voltage	$V_{DF}$	_	0.9	_	V	I <sub>F</sub> = 30 A, V <sub>GS</sub> = 0
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	110	_	ns	$I_F = 30 \text{ A}, V_{GS} = 0$ $di_F/dt = 50 \text{ A}/\mu\text{s}$
Over load shut down	t <sub>os1</sub>	_	0.34	_	ms	$V_{GS} = 5 \text{ V}, V_{DD} = 16 \text{ V}$
operation time Note 6	t <sub>os2</sub>		0.23		ms	$V_{GS} = 5 \text{ V}, V_{DD} = 24 \text{ V}$

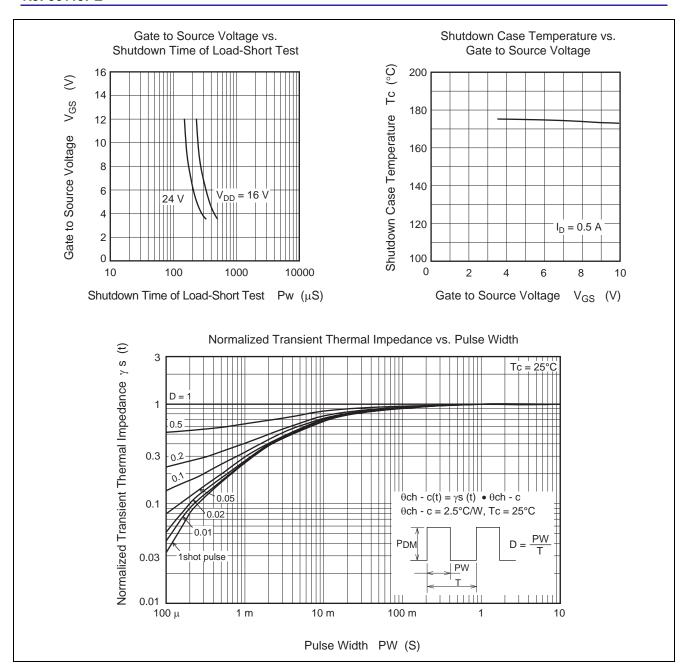
Notes: 5. Pulse test

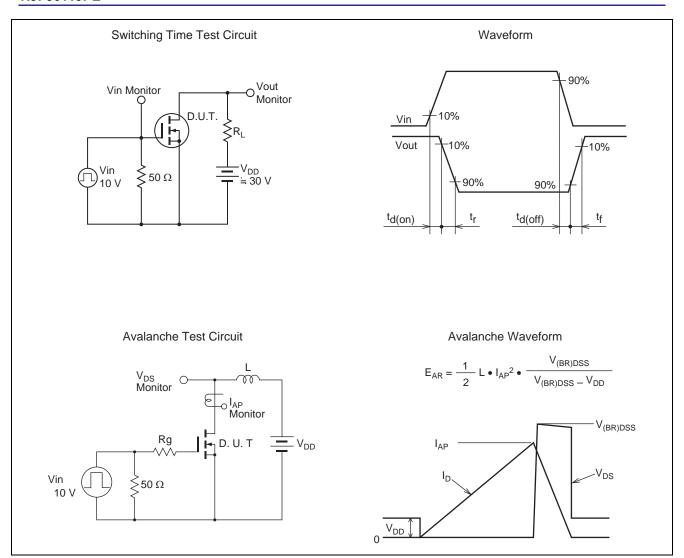
6. Including the junction temperature rise of the over loaded condition.

#### **Main Characteristics**

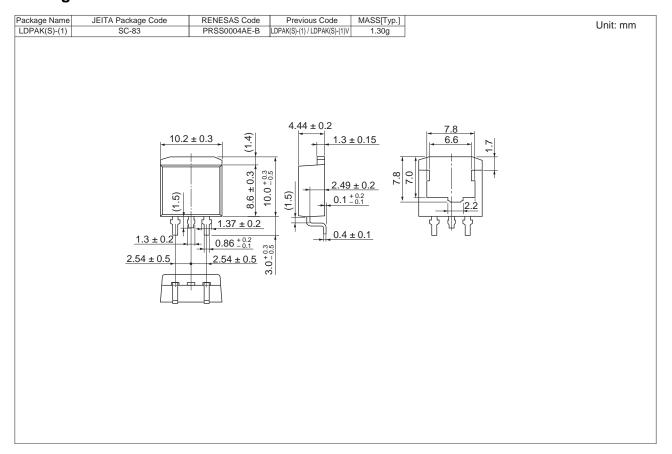








## **Package Dimensions**



# **Ordering Information**

Orderable Part Number	Quantity	Shipping Container
RJF0611JPE-00-J3	1000 pcs	Taping

Note: The symbol of 2nd "-" is occasionally presented as "#".

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